



BOX AF

AF  
2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

INOUE et al.

Serial Number: 09/473,988

Filed: December 29, 1999

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

Group Art Unit: 2814

Examiner: T. Doan

# 17/D  
4-26-02  
71002

AMENDMENT AFTER FINAL REJECTION

BOX AF

Commissioner for Patents  
Washington, D.C. 20231

April 22, 2002

Sir:

In response to the Office Action dated January 25, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

RECEIVED  
APR 24 2002  
TECHNOLOGY CENTER 2800

Please amend claims 1, 2 and 7-9 as follows:

1. (Four Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:
- a first insulating layer of a composition containing SiH;
  - a second insulating layer formed on said first insulating layer; and
  - a third insulating layer formed between said conductive film and said first insulating layer,

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